

# P-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	- 40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.075			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.145			
I <sub>D</sub> (A)	- 4.6			
Configuration	Single			

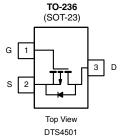
<u> Din-Tek</u>

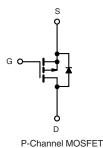
# FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- AEC-Q101 Qualified<sup>c</sup>
- 100 % R<sub>q</sub> and UIS Tested
- Compliant to RoHS Directive 2002/95/EC









ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and Halogen-free	DTS4501

ABSOLUTE MAXIMUM RATINGS	<b>S</b> (T <sub>C</sub> = 25 °C, unles	s otherwise noted	d)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		$V_{DS}$	- 40	V	
Gate-Source Voltage		V <sub>GS</sub>	± 20	V	
Continuous Drain Current	T <sub>C</sub> = 25 °C	1	- 4.6		
	T <sub>C</sub> = 125 °C	I <sub>D</sub>	- 2.6		
Continuous Source Current (Diode Conduction)		Is	- 3.7	Α	
Pulsed Drain Current <sup>a</sup>		I <sub>DM</sub>	- 18		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	- 12		
Single Pulse Avalanche Energy	L = 0.1 MH	E <sub>AS</sub>	7.2	mJ	
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	P <sub>D</sub>	3	14/	
	T <sub>C</sub> = 125 °C		1	W	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount <sup>b</sup>	$R_{thJA}$	166	°C/W
Junction-to-Foot (Drain)		R <sub>thJF</sub>	50	G/W

#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. When mounted on 1" square PCB (FR-4 material).
- c. Parametric verification ongoing.

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PARAMETER	SYMBOL	vise noted)  TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static						ı	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0, I <sub>D</sub> = - 250 μA		- 40	-	=.	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = - 250 μA	- 1.5	- 2.0	- 2.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 40 V	-	-	- 1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = - 40 V, T <sub>J</sub> = 125 °C	-	-	- 50	μΑ
		$V_{GS} = 0 V$	V <sub>DS</sub> = - 40 V, T <sub>J</sub> = 175 °C	-	-	- 150	1
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = - 10 V	V <sub>DS</sub> ≤ - 5 V	- 10	-	-	Α
		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 3 A	-	0.061	0.075	
Drain-Source On-State Resistance <sup>a</sup>	В	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 3 A, T <sub>J</sub> = 125 °C	-	-	0.116	Ω
	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 3 A, T <sub>J</sub> = 175 °C	-	-	0.139	
		V <sub>GS</sub> = - 4.5 V	I <sub>D</sub> = - 2.4 A	-	0.120	0.145	
Forward Transconductanceb	9 <sub>fs</sub>	V <sub>DS</sub> :	= - 5 V, I <sub>D</sub> = - 3 A	-	8	-	S
Dynamic <sup>b</sup>	•						
Input Capacitance	C <sub>iss</sub>			-	493	620	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>GS</sub> = 0 V V <sub>DS</sub> = - 25 V, f = 1 MHz		76	95	рF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	51	65	1
Total Gate Charge <sup>c</sup>	Qg			-	10.5	16	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} = -20 \text{ V}, I_{D} = -3 \text{ A}$	-	1.8	-	nC
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	2.6	-	
Gate Resistance	R <sub>g</sub>	f = 1 MHz		5	10	15	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	5	8	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = - 20 V, $R_L$ = 6.7 $\Omega$ $I_D \cong$ - 3 A, $V_{GEN}$ = - 10 V, $R_g$ = 1 $\Omega$		-	11	17	ns
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	19	29	
Fall Time <sup>c</sup>	t <sub>f</sub>			-	8	12	
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	- 18	Α
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> =	- 1.5 A, V <sub>GS</sub> = 0	-	- 0.8	- 1.2	V

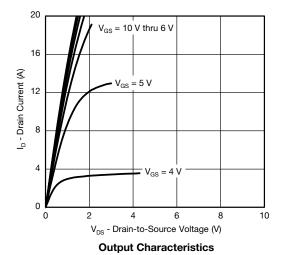
#### Notes

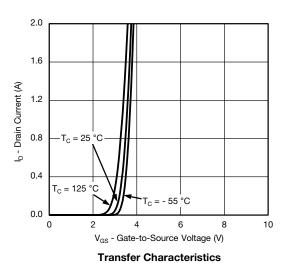
- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

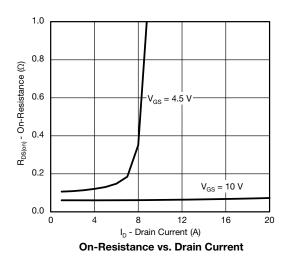
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

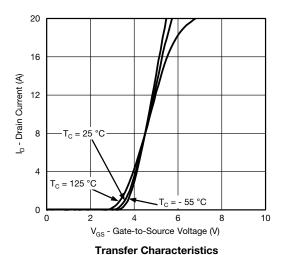


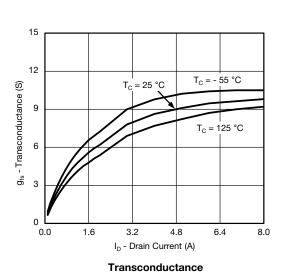
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

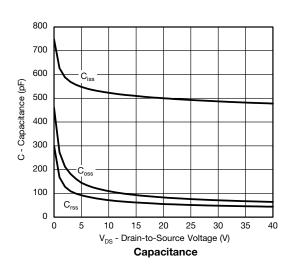












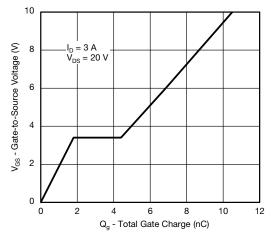


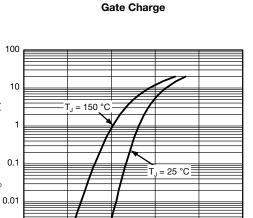
I<sub>S</sub> - Source Current (A)

0.001

0.0

## **TYPICAL CHARACTERISTICS** ( $T_A = 25 \, ^{\circ}\text{C}$ , unless otherwise noted)

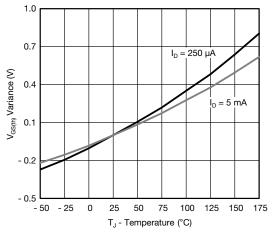




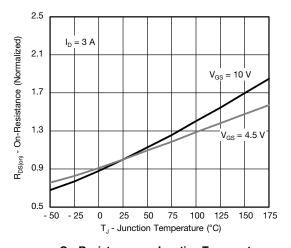
 $\label{eq:VSD} V_{SD} \text{ - Source-to-Drain Voltage (V)}$  Source Drain Diode Forward Voltage

1.2

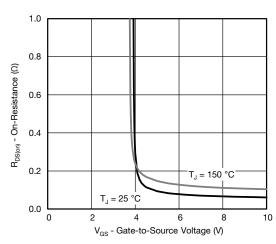
1.5



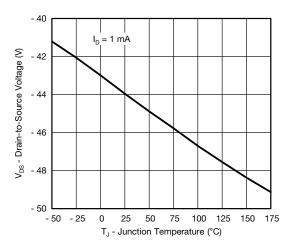
Threshold Voltage



On-Resistance vs. Junction Temperature



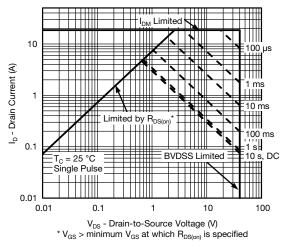
On-Resistance vs. Gate-to-Source Voltage



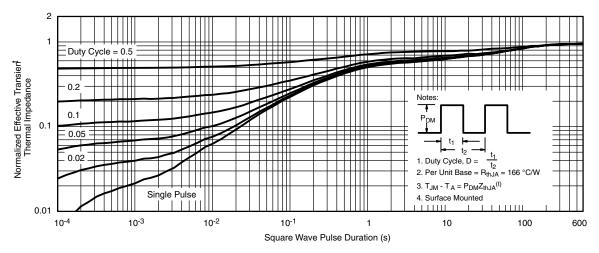
**Drain Source Breakdown vs. Junction Temperature** 



## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



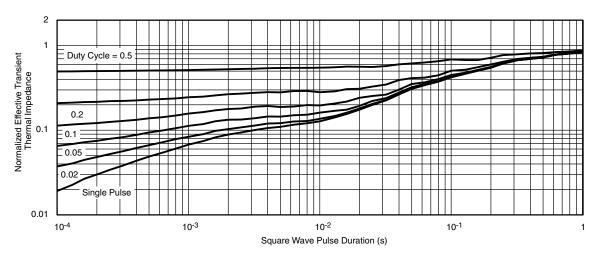
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



## **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



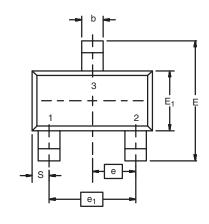
#### Normalized Thermal Transient Impedance, Junction-to-Ambient

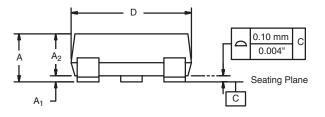
#### Note

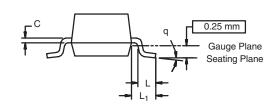
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



### SOT-23 (TO-236): 3-LEAD







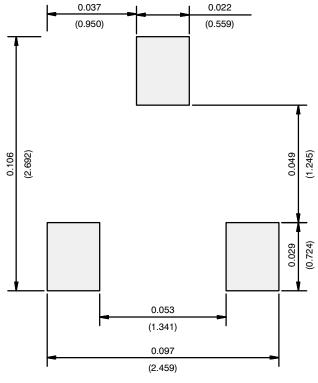
Dim	MILLIM	IETERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A <sub>1</sub>	0.01	0.10	0.0004	0.004	
A <sub>2</sub>	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E <sub>1</sub>	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e <sub>1</sub>	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L <sub>1</sub>	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	

ECN: S-03946-Rev. K, 09-Jul-01

DWG: 5479



#### **RECOMMENDED MINIMUM PADS FOR SOT-23**



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



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